

isc Silicon NPN Power Transistor

2SD357

DESCRIPTION

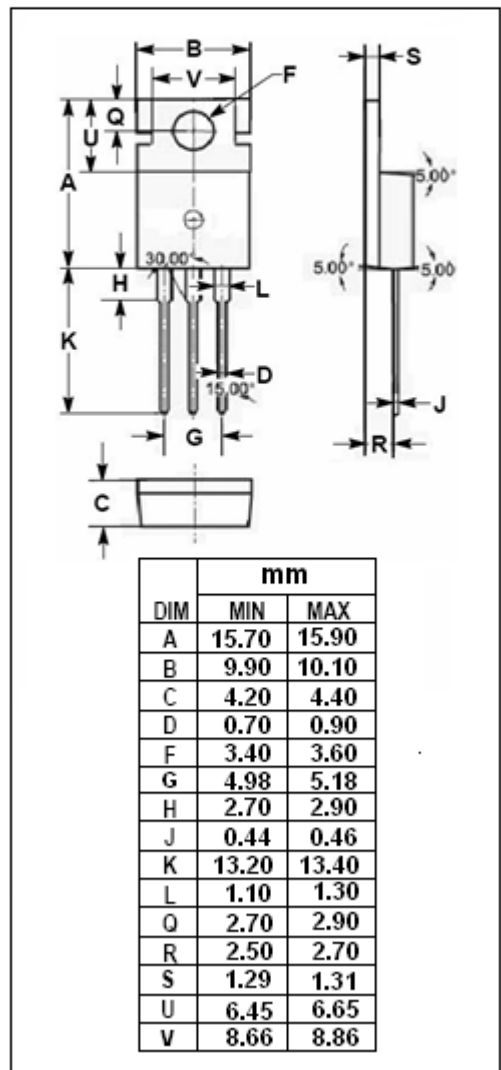
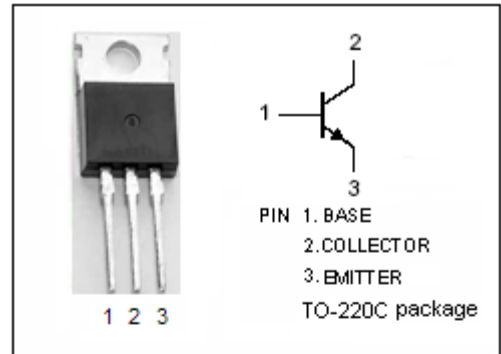
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 100V(\text{Min})$
- Good Linearity of h_{FE}
- Complement to Type 2SB527

APPLICATIONS

- Designed for AF high power dirver applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	110	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	0.8	A
P_C	Collector Power Dissipation @ $T_a=25^{\circ}C$	1	W
	Collector Power Dissipation @ $T_c=25^{\circ}C$	10	
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon NPN Power Transistor**2SD357****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; R_{BE}=\infty$	100			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}; I_E=0$	110			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}; I_C=0$	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=0.3\text{A}; I_B=30\text{mA}$			1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=50\text{mA}; V_{CE}=4\text{V}$		0.7		V
I_{CBO}	Collector Cutoff Current	$V_{CB}=25\text{V}; I_E=0$			10	μA
I_{CEO}	Collector Cutoff Current	$V_{CE}=100\text{V}; R_{BE}=\infty$			1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			10	μA
h_{FE}	DC Current Gain	$I_C=0.3\text{A}; V_{CE}=4\text{V}$	55		300	

◆ **h_{FE} Classifications**

C	D	E
55-110	90-180	150-300